This improved full addrer performs the addition of two 4-bit binary numbers. The sum (Σ) outputs are provided for each bit and the resultant carry (C4) is obtained from the fourth bit. This adder features full internal look ahead across all four bit generating the carry term in ten nanoseconds typically. This provides the system designer with partial look-ahead performance at the economy and reduced package count of a ripple-carry implementation.

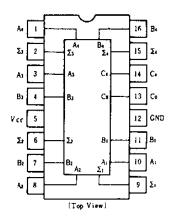
EFUNCTION TABLE

				Outputs							
	Inp	uts		When C0 =		When C2=L	When C0 =		When C2=H		
A ₁ /	B ₁	A ₂	B ₂	Σ1/	Σ_2	C2/	Σ1/	Σ2/	C ₂		
<u>/A</u> 3	B 3	Αı	∕B₁	$\sqrt{\Sigma_3}$	∕Σι	∕C₁	$\sqrt{\Sigma_3}$	⁄Σ,	∕C₄		
L	L	L	L	ı.	L	L	Н	L	L		
Н	L	L	L	Н	L	L	L	Н	L		
L	Н	L	L	Н	L	L	L	Н	L		
Н	Н	L	L	L.	Н	L	Н	Н	L		
L	L	Н	L.	Į,	Н	L	Н	Н	L		
Н	L	Н	L.	Н	Н	L	L.	L.	Н		
L.	Н	Н	L	H	Н	Ĺ	L	L	H		
Н	Н	Н	L	L.	L	Н	Н	L	Н		
_ L	L	L	Н	L.	Н	Ĺ	Н	Н	L		
Н	L	L	H	H	Н	L	L	L	Н		
_L	Н	L	Н	H	Н	L	L	L	Н		
Н	H	L	Н	L.	L	Н	Н	L	Н		
L	Ĺ	H	Н	L	L	Н	Н	L	Н		
Н	L	Н	Н	H	L	Н	L	H	Н		
L	Н	Н	Н	Н	L	Н	L	Н	Н		
<u>H</u>	Н	Н	Н	L.	Н	Н	Н	Н	Н		

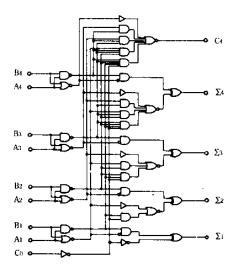
H; high level, L; low level, X; irrelevant

Note) Input conditions at A1, B1, A2, B2, and C0 are used to determine outputs Σ1 and Σ2 and the value of the internal carry
 C2. The value at C2, A3, B3, A4, and B4 are than used to determine outputs Σ3, Σ4 and C4.

■PIN ARRANGEMENT



■BLOCK DIAGRAM



ELECTRICAL CHARACTERISTICS ($Ta = -20 \sim +75^{\circ}C$)

Item		Symbol	Symbol Test Conditions				max	Unit	
		ViH			2.0			ν	
Input voita	ge	V_{II} .					0.8	V	
Output voltage		Von	$V_{CC} = 4.75 \text{ V}, V_{IH} + 2 \text{ V}, V_{IL} = 0.8 \text{ V}.$	2.7			V		
			$V_{CC} = 4.75 \text{V}$, $V_{IH} + 2 \text{V}$	<i>Io1.</i> = 4mA			0.4	V	
		Vot.	$V_{IL} = 0.8 \mathrm{V}$	Int = 8mA			0.5		
except C0							40	иА	
Ę.	C0	— IiB	$V_{CC} = 5.25 \mathrm{V}, V_{F} = 2.7 \mathrm{V}$				20		
E except C0	except C0						-0.8	A	
			$V_{CC} = 5.25 \text{V}, V_{I} \approx 0.4 \text{V}$				0.4	mΑ	
except C0							0.2		
1	CO	\Box I_{t}	Vcc = 5.25V, $Vt = 7V$				0.1	mА	
Short circ	uit output current	los	V _{CC} = 5.25V			-	-100	m A	
Supply current		1		All inputs = 0V	-	22	39		
		Ic c	$V_{CC} \sim 5.25 \mathrm{V}$	B input 0.8V, Other inputs4.5V		19	34	mΑ	
		!	All inputs4.5V		_	19	34		
Input clamp voltage		V_{IK}	Vec 4.75V, IIN = = 18mA				-1.5	V	

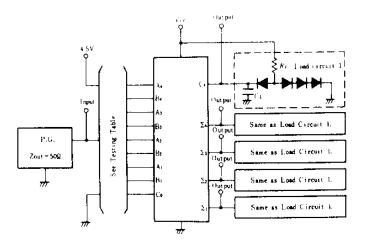
^{*} VCC=5V, Ta-25 $^{\circ}C$

ESWITCHING CHARACTERISTICS ($V_{CC} = 5V$, $T_a = 25^{\circ}C$)

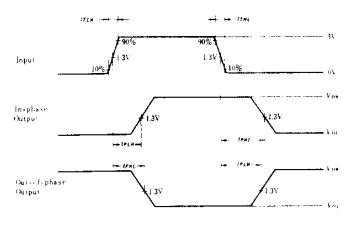
ltem .	Symbol	Inputs	Outputs	Test Conditions	min	typ	max	Unit
	tri.B		Σ.			16	24	ns
	tem	C_{a}			15	24	ns	
	trisi	A., B.	Σ.	$Ci = 15 \mathrm{pF}, Ri = 2 \mathrm{k}\Omega$		15	24	ns.
	tem					15	24	ns
Propagation delay time	tra.n		. C		-	11	17	ns
	ten	C_0				15	22	ns
	triai		Cı			11	17	ns
	trui	A., B.				12	17	ns

TESTING METHOD

1) Test Circuit



Waveform

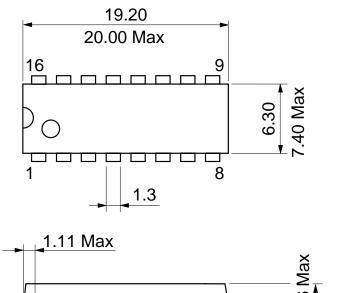


- Notes) 1. Input pulse; $t_{TLH} \le 15 \text{ ns}$, $t_{THL} \le 6 \text{ ns}$, PRR = 1 MHz, duty cycle=50%
 - C_L includes probe and jig capacitance.
 All diodes are 1S2074 (f).

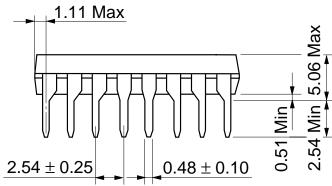
2) Testing Table

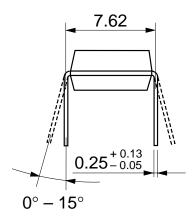
Item	From input to output	Inputs									Outputs	3			
		B ₄	A4	B ₃	A3	B2	A ₂	Bı	A ₁	Co	C ₄	Σ4	Σ3	Σ2	Σι
••••	Co	GND	GND	GND	GND	GND	GND	GND	GND	IN					OUT
	→Σ, or C4	GND	4.5V	GND	4.5V	GND	4.5V	GND	4.5V	IN	OUT	OUT	OUT	OUT	OUT
		CND	GND	GND	CND	GND	GND	GND	IN	GND					OUT
		GND			GND			IN	GND	GND		L			001
		GND	GND	GND	CND	GND	D IN	GND	GND	GND		_ _		оит	
					GND	IN	GND	GND	UND	GND					
		GND	GND	GND	IN	GND	GND	GND	GND	GND			OUT		
				IN	GND	GND									
tplh	A; or B; →Σ; or C4	GND	IN	GND	GND	GND	GND	GND	GND	GND		OUT			
<i>tphl</i>		IN	GND												
		GND	GND	GND	GND	GND	GND	4.5V	IN	GND				OUT	OUT
								IN	4.5V						
		GND	GND	GND	GND	4.5V	IN	GND	GND	GND			OUT	OUT	
					0.10	IN	4.5V	3			ļ				
		GND GN	GND	4.5V	IN	GND	GND	GND	GND	GND		OUT	OUT		
			GND	IN	4.5V	Ginb	J.	0.11			<u> </u>				
		4.5V	IN	GND GNE	GND	GND	GND	GND	ND GND	GND	оит	оит	- •		
		IN	4.5V	UND	J. C.	GIVD		GND						<u>L</u>	

Unit: mm



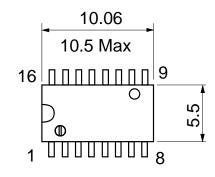


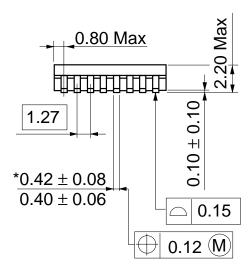




Hitachi Code	DP-16
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.07 g

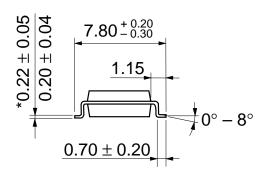
Unit: mm





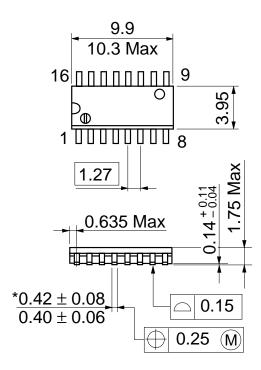
*Dimension including the plating thickness
Base material dimension



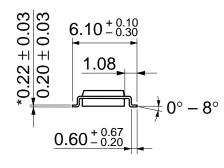


Hitachi Code	FP-16DA
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.24 g

Unit: mm







*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DN
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.15 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose,CA 95134 Tel: <1> (408) 433-1990 Fax: <1>(408) 433-0223 Hitachi Europe GmbH Electronic components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich Germany

Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd. Flectronic Components Group Whitebrook Park Lower Cookham Road Maidenhead

Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office

3F, Hung Kuo Building. No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd. Group III (Electronic Components) 7/F., North Tower, World Finance Centre, Harbour City, Canton Road, Tsim Sha Tsui, Kowloon, Hong Kong Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281

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